

L Number	Hits	Search Text	DB	Time stamp
149	90140	low adj voltage	USPAT; US-PGPUB	2004/09/08 18:54
150	140305	high adj voltage	USPAT; US-PGPUB	2004/09/08 18:59
151	79147	silicon adj nitride	USPAT; US-PGPUB	2004/09/08 18:59
152	5606	"Si.sub.3N.sub.4"	USPAT; US-PGPUB	2004/09/08 19:00
153	956	Si3N4	USPAT; US-PGPUB	2004/09/08 19:00
154	345	"Si.sub.xN.sub.y"	USPAT; US-PGPUB	2004/09/08 19:00
155	96	SixNy	USPAT; US-PGPUB	2004/09/08 19:00
156	136137	silicon adj \$2oxide	USPAT; US-PGPUB	2004/09/08 19:01
157	133914	"SiO.sub.2"	USPAT; US-PGPUB	2004/09/08 19:01
158	6893	SiO2	USPAT; US-PGPUB	2004/09/08 19:01
159	9915	gate adj dielectric	USPAT; US-PGPUB	2004/09/08 19:01
160	28282	gate adj insulat\$3	USPAT; US-PGPUB	2004/09/08 19:02
161	558	(low adj voltage) and (high adj voltage) and (((silicon adj nitride) or "Si.sub.3N.sub.4" or Si3N4 or "Si.sub.xN.sub.y" or SixNy) same ((gate adj dielectric) or (gate adj insulat\$3))) and (((silicon adj \$2oxide) or "SiO.sub.2" or SiO2) same ((gate adj dielectric) or (gate adj insulat\$3)))	USPAT; US-PGPUB	2004/09/08 19:16
162	2898	dual adj gate	USPAT; US-PGPUB	2004/09/08 19:16
163	326	(dual adj gate) and (((silicon adj nitride) or "Si.sub.3N.sub.4" or Si3N4 or "Si.sub.xN.sub.y" or SixNy) same ((gate adj dielectric) or (gate adj insulat\$3))) and (((silicon adj \$2oxide) or "SiO.sub.2" or SiO2) same ((gate adj dielectric) or (gate adj insulat\$3)))	USPAT; US-PGPUB	2004/09/08 19:17

L Number	Hits	Search Text	DB	Time stamp
-	6	((("6294421") or ("6110842") or ("6030862") or ("5960289") or ("6262455") or ("6037224")).PN.	USPAT; US-PGPUB	2004/09/08 15:23
-	42	dual adj2 oxide adj thickness	USPAT; US-PGPUB	2004/09/08 15:24
-	1	dual adj2 insulat\$3 adj thickness	USPAT; US-PGPUB	2004/09/08 15:24
-	11	dual adj2 dielectric adj thickness	USPAT; US-PGPUB	2004/09/08 15:25
-	2	multiple adj2 dielectric adj thickness	USPAT; US-PGPUB	2004/09/08 15:25
-	1	multiple adj2 insulat\$3 adj thickness	USPAT; US-PGPUB	2004/09/08 15:25
-	29	multiple adj2 oxide adj thickness	USPAT; US-PGPUB	2004/09/08 15:26
-	2778	(clean\$3 or remov\$3 or etch\$3) near3 (native adj oxide)	USPAT; US-PGPUB	2004/09/08 15:28
-	0	((dual adj2 oxide adj thickness) or (dual adj2 insulat\$3 adj thickness) or (dual adj2 dielectric adj thickness) or (multiple adj2 dielectric adj thickness) or (multiple adj2 insulat\$3 adj thickness) or (multiple adj2 oxide adj thickness)) and ((clean\$3 or remov\$3 or etch\$3) near3 (native adj oxide))	USPAT; US-PGPUB	2004/09/08 15:28
-	2277279	clean\$3 or remov\$3 or etch\$3	USPAT; US-PGPUB	2004/09/08 15:28
-	77	((dual adj2 oxide adj thickness) or (dual adj2 insulat\$3 adj thickness) or (dual adj2 dielectric adj thickness) or (multiple adj2 dielectric adj thickness) or (multiple adj2 insulat\$3 adj thickness) or (multiple adj2 oxide adj thickness)) and (clean\$3 or remov\$3 or etch\$3)	USPAT; US-PGPUB	2004/09/08 15:29